

N-channel 800 V, 0.59 Ω typ., 6 A MDmesh™ K5 Power MOSFET in a PowerFLAT™ 5x6 VHV package

Datasheet - production data

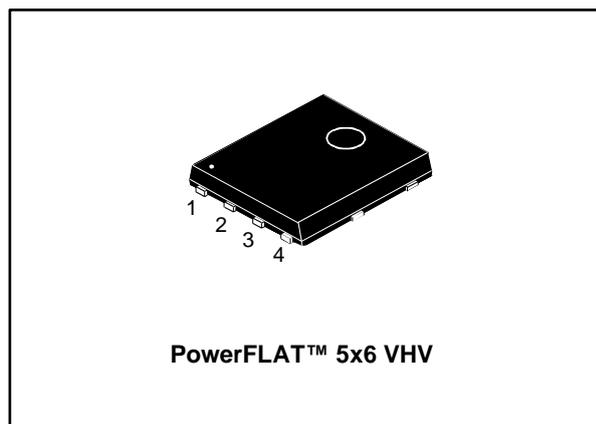
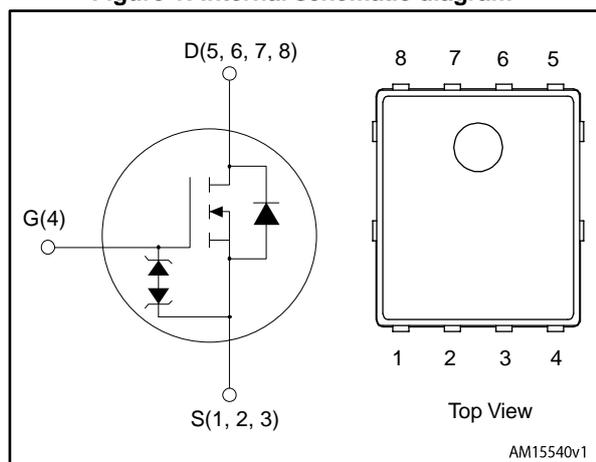


Figure 1: Internal schematic diagram



Features

Order code	V _{DS}	R _{DS(on)} max.	I _D
STL10LN80K5	800 V	0.66 Ω	6 A

- Industry's lowest R_{DS(on)} x area
- Industry's best figure of merit (FoM)
- Ultra-low gate charge
- 100% avalanche tested
- Zener-protected

Applications

- Switching applications

Description

This very high voltage N-channel Power MOSFET is designed using MDmesh™ K5 technology based on an innovative proprietary vertical structure. The result is a dramatic reduction in on-resistance and ultra-low gate charge for applications requiring superior power density and high efficiency.

Table 1: Device summary

Order code	Marking	Package	Packing
STL10LN80K5	10LN80K5	PowerFLAT™ 5x6 VHV	Tape and reel

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1 Electrical ratings

Table 2: Absolute maximum ratings

Symbol	Parameter	Value	Unit
V_{GS}	Gate-source voltage	± 30	V
I_D	Drain current (continuous) at $T_C = 25\text{ }^\circ\text{C}$	6	A
I_D	Drain current (continuous) at $T_C = 100\text{ }^\circ\text{C}$	3.8	A
$I_D^{(1)}$	Drain current pulsed	24	A
P_{TOT}	Total dissipation at $T_C = 25\text{ }^\circ\text{C}$	42	W
$dv/dt^{(2)}$	Peak diode recovery voltage slope	4.5	V/ns
$dv/dt^{(3)}$	MOSFET dv/dt ruggedness	50	
T_j	Operating junction temperature range	- 55 to 150	$^\circ\text{C}$
T_{stg}	Storage temperature range		

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾ $I_{SD} \leq 6\text{ A}$, $dv/dt \leq 100\text{ A}/\mu\text{s}$; $V_{DS\text{ peak}} < V_{(BR)DSS}$, $V_{DD}=640\text{ V}$

⁽³⁾ $V_{DS} \leq 640\text{ V}$

Table 3: Thermal data

Symbol	Parameter	Value	Unit
$R_{thj-case}$	Thermal resistance junction-case	3	$^\circ\text{C}/\text{W}$
$R_{thj-amb}^{(1)}$	Thermal resistance junction-ambient	59	$^\circ\text{C}/\text{W}$

Notes:

⁽¹⁾When mounted on 1inch² FR-4 board, 2 oz Cu

Table 4: Avalanche characteristics

Symbol	Parameter	Value	Unit
I_{AR}	Avalanche current, repetitive or not repetitive (pulse width limited by T_{jmax})	2.7	A
E_{AS}	Single pulse avalanche energy (starting $T_j = 25\text{ }^\circ\text{C}$, $I_D = I_{AR}$, $V_{DD} = 50\text{ V}$)	240	mJ

2 Electrical characteristics

$T_C = 25\text{ °C}$ unless otherwise specified

Table 5: On/off-state

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$V_{(BR)DSS}$	Drain-source breakdown voltage	$V_{GS} = 0\text{ V}$, $I_D = 1\text{ mA}$	800			V
I_{DSS}	Zero gate voltage drain current	$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$			1	μA
		$V_{GS} = 0\text{ V}$, $V_{DS} = 800\text{ V}$ $T_C = 125\text{ °C}$ ⁽¹⁾			50	μA
I_{GSS}	Gate body leakage current	$V_{DS} = 0\text{ V}$, $V_{GS} = \pm 20\text{ V}$			± 10	μA
$V_{GS(th)}$	Gate threshold voltage	$V_{DS} = V_{GS}$, $I_D = 100\text{ }\mu\text{A}$	3	4	5	V
$R_{DS(on)}$	Static drain-source on-resistance	$V_{GS} = 10\text{ V}$, $I_D = 4\text{ A}$		0.59	0.66	Ω

Notes:

⁽¹⁾Defined by design, not subject to production test.

Table 6: Dynamic

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
C_{iss}	Input capacitance	$V_{DS} = 100\text{ V}$, $f = 1\text{ MHz}$, $V_{GS} = 0\text{ V}$	-	427	-	pF
C_{oss}	Output capacitance		-	43	-	pF
C_{rss}	Reverse transfer capacitance		-	0.25	-	pF
$C_{o(tr)}$ ⁽¹⁾	Equivalent capacitance time related	$V_{DS} = 0\text{ to }640\text{ V}$, $V_{GS} = 0\text{ V}$	-	72	-	pF
$C_{o(er)}$ ⁽²⁾	Equivalent capacitance energy related			27	-	pF
R_g	Intrinsic gate resistance	$f = 1\text{ MHz}$, $I_D = 0\text{ A}$	-	7	-	Ω
Q_g	Total gate charge	$V_{DD} = 640\text{ V}$, $I_D = 8\text{ A}$	-	15	-	nC
Q_{gs}	Gate-source charge	$V_{GS} = 10\text{ V}$	-	4.2	-	nC
Q_{gd}	Gate-drain charge	(see Figure 16: "Test circuit for gate charge behavior")	-	9	-	nC

Notes:

⁽¹⁾Time related is defined as a constant equivalent capacitance giving the same charging time as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

⁽²⁾Energy related is defined as a constant equivalent capacitance giving the same stored energy as C_{oss} when V_{DS} increases from 0 to 80% V_{DSS}

Table 7: Switching times

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
$t_{d(on)}$	Turn-on delay time	$V_{DD} = 400\text{ V}$, $I_D = 4\text{ A}$, $R_G = 4.7\ \Omega$ $V_{GS} = 10\text{ V}$ (see Figure 15: "Test circuit for resistive load switching times" and Figure 20: "Switching time waveform")	-	11.8	-	ns
t_r	Rise time		-	10	-	ns
$t_{d(off)}$	Turn-off delay time		-	28	-	ns
t_f	Fall time		-	13	-	ns

Table 8: Source-drain diode

Symbol	Parameter	Test conditions	Min.	Typ.	Max.	Unit
I_{SD}	Source-drain current		-		6	A
$I_{SDM}^{(1)}$	Source-drain current (pulsed)		-		24	A
$V_{SD}^{(2)}$	Forward on voltage	$I_{SD} = 6\text{ A}$, $V_{GS} = 0\text{ V}$	-		1.5	V
t_{rr}	Reverse recovery time	$I_{SD} = 6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$ (see Figure 17: "Test circuit for inductive load switching and diode recovery times")	-	350		ns
Q_{rr}	Reverse recovery charge		-	3.9		μC
I_{RRM}	Reverse recovery current		-	22.5		A
t_{rr}	Reverse recovery time	$I_{SD} = 6\text{ A}$, $di/dt = 100\text{ A}/\mu\text{s}$, $V_{DD} = 60\text{ V}$, $T_j = 150\text{ }^\circ\text{C}$ (see Figure 17: "Test circuit for inductive load switching and diode recovery times")	-	505		ns
Q_{rr}	Reverse recovery charge		-	5		μC
I_{RRM}	Reverse recovery current		-	20		A

Notes:

⁽¹⁾Pulse width limited by safe operating area

⁽²⁾Pulsed: pulse duration = 300 μs , duty cycle 1.5%

Table 9: Gate-source Zener diode

Symbol	Parameter	Test conditions	Min	Typ.	Max	Unit
$V_{(BR)GSO}$	Gate-source breakdown voltage	$I_{GS} = \pm 1\text{ mA}$, $I_D = 0\text{ A}$	30	-	-	V

The built-in back-to-back Zener diodes are specifically designed to enhance the ESD performance of the device. The Zener voltage facilitates efficient and cost-effective device integrity protection, thus eliminating the need for additional external componentry.

2.2 Electrical characteristics (curves)

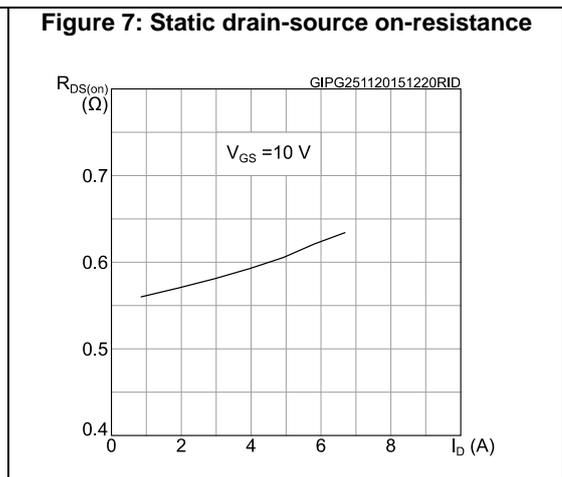
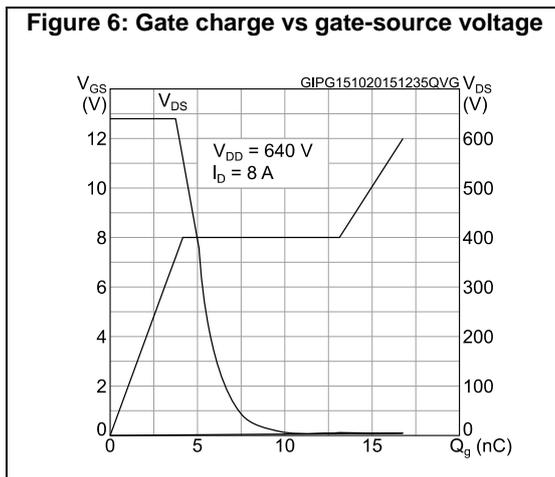
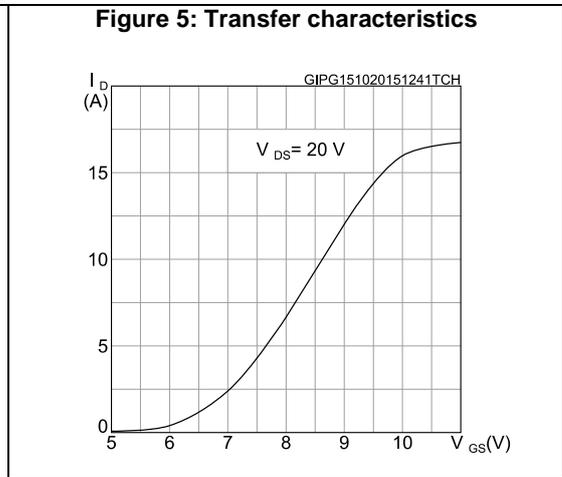
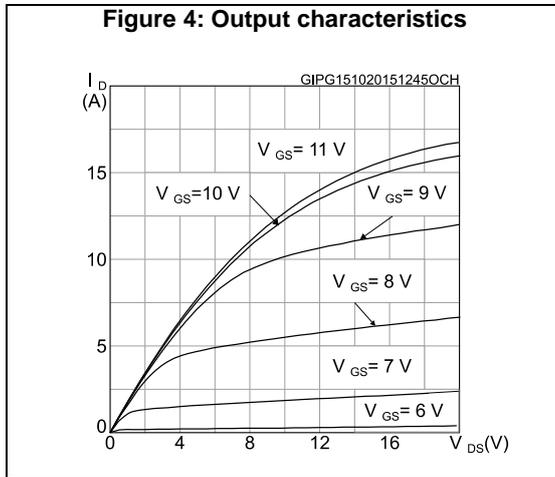
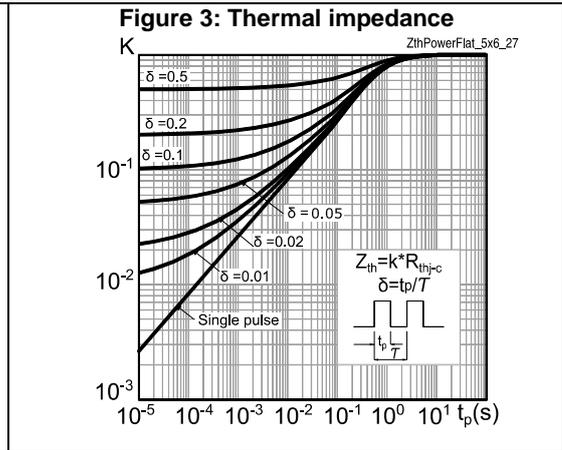
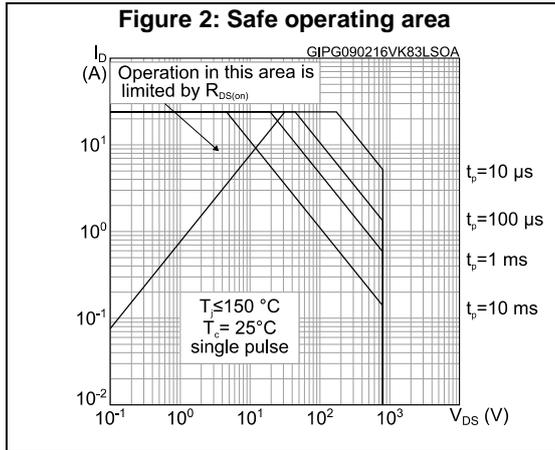


Figure 8: Capacitance variations

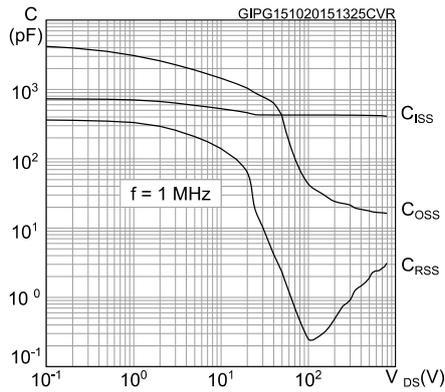


Figure 9: Normalized gate threshold voltage vs temperature

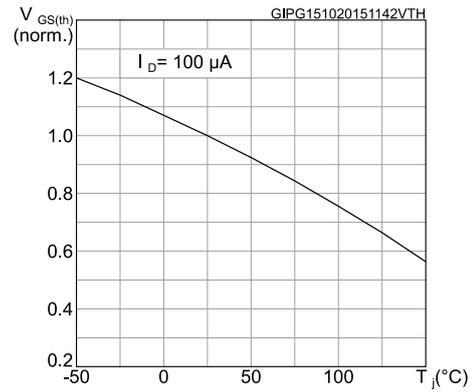


Figure 10: Normalized on-resistance vs temperature

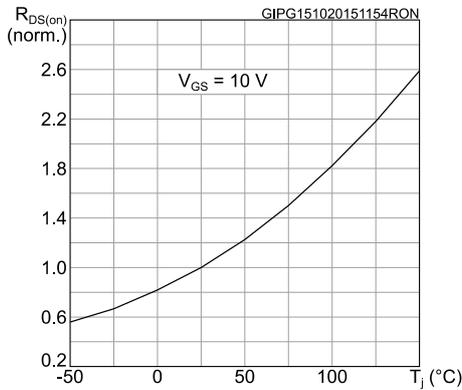


Figure 11: Normalized V(BR)DSS vs temperature

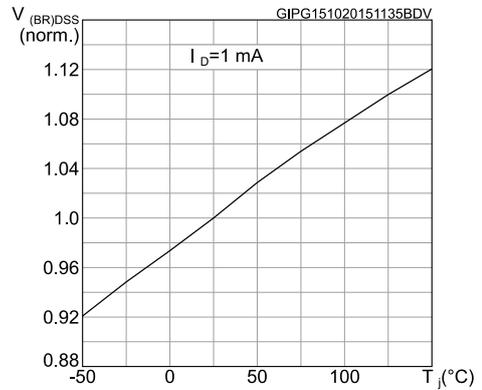


Figure 12: Output capacitance stored energy

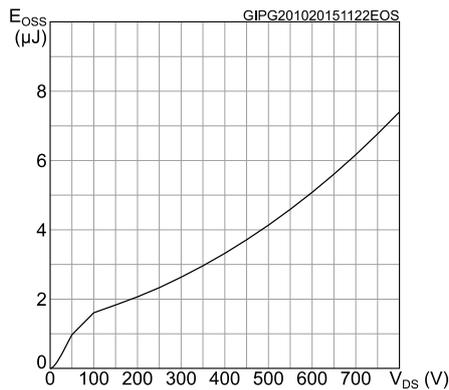


Figure 13: Source-drain diode forward characteristics

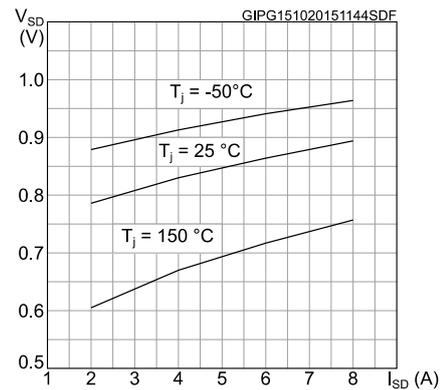
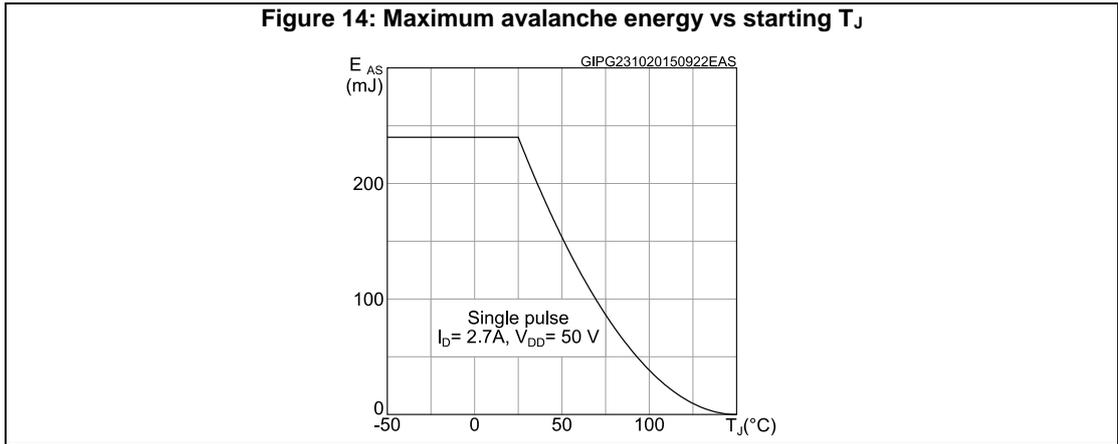
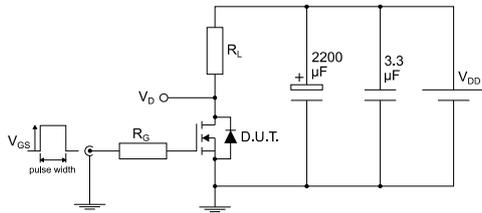


Figure 14: Maximum avalanche energy vs starting T_J



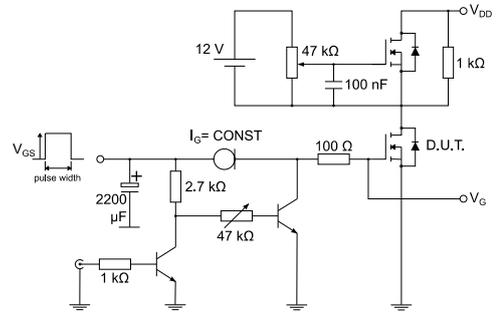
3 Test circuits

Figure 15: Test circuit for resistive load switching times



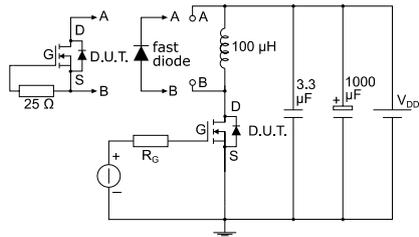
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Figure 16: Test circuit for gate charge behavior



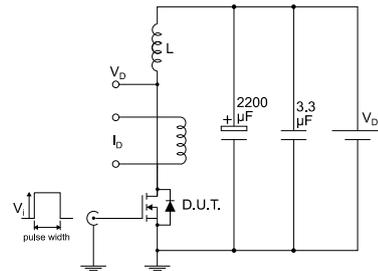
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Figure 17: Test circuit for inductive load switching and diode recovery times



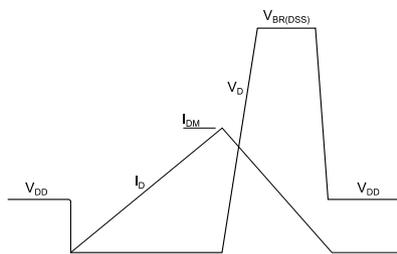
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Figure 18: Unclamped inductive load test circuit



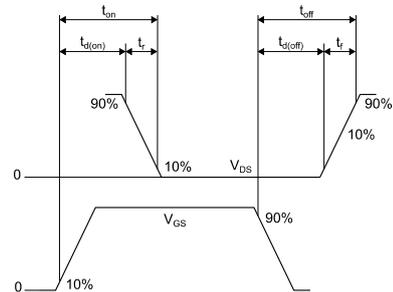
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Figure 19: Unclamped inductive waveform



AM01472v1

Figure 20: Switching time waveform



AM01473v1

4 Package information

In order to meet environmental requirements, ST offers these devices in different grades of ECOPACK[®] packages, depending on their level of environmental compliance. ECOPACK[®] specifications, grade definitions and product status are available at: www.st.com. ECOPACK[®] is an ST trademark.

4.1 PowerFLAT™ 5x6 VHV package information

Figure 21: PowerFLAT™ 5x6 VHV Package outline

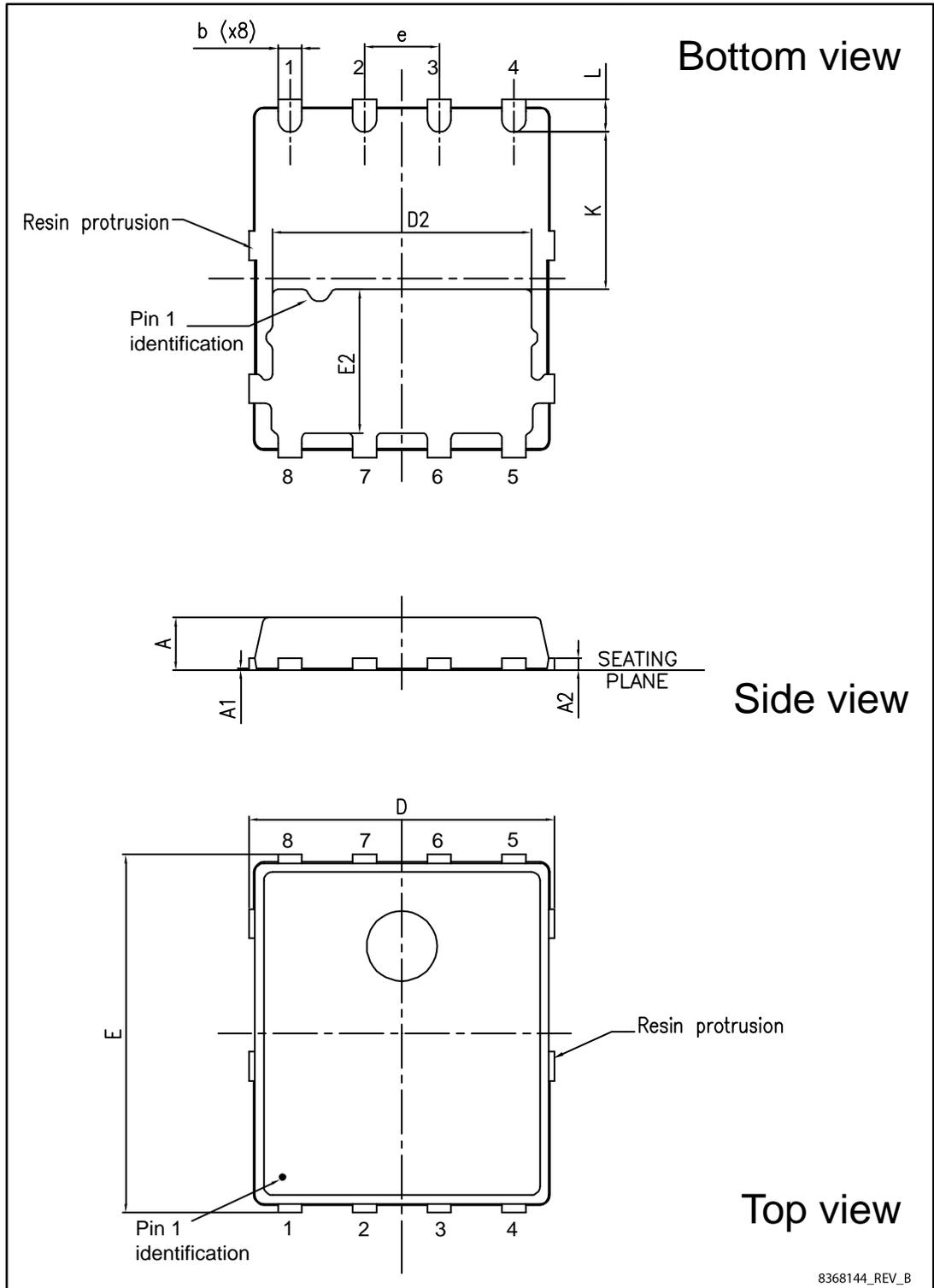
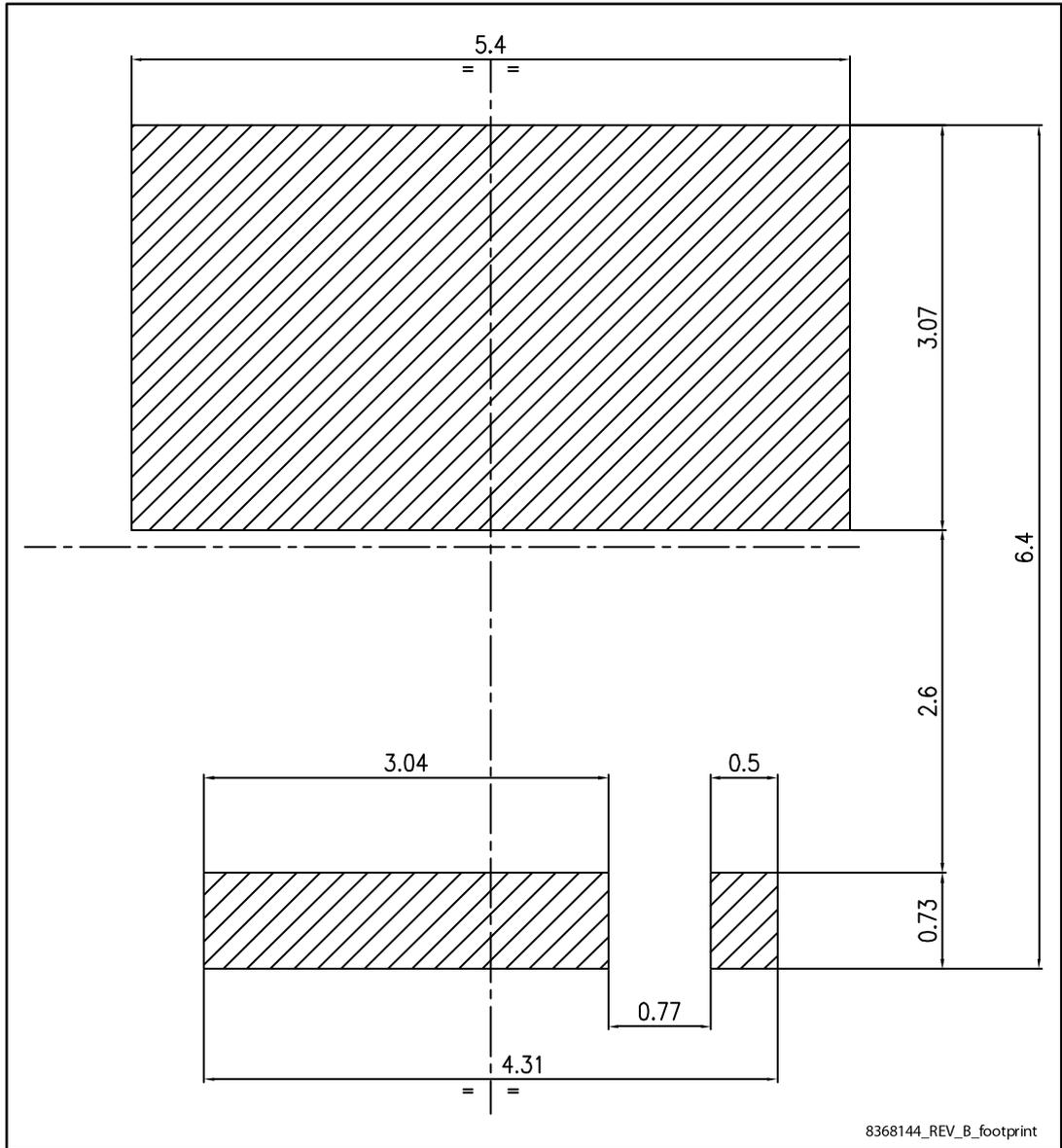


Table 10: PowerFLAT™ 5x6 VHV package mechanical data

Dim.	mm		
	Min.	Typ.	Max.
A	0.80		1.00
A1	0.02		0.05
A2		0.25	
b	0.30		0.50
D	5.00	5.20	5.40
E	5.95	6.15	6.35
D2	4.30	4.40	4.50
E2	2.40	2.50	2.60
e		1.27	
L	0.50	0.55	0.60
K	2.60	2.70	2.80

Figure 22: PowerFLAT™ 5x6 VHV recommended footprint (dimensions are in mm)



4.2 PowerFLAT™ 5x6 packing information

Figure 23: PowerFLAT™ 5x6 tape (dimensions are in mm)

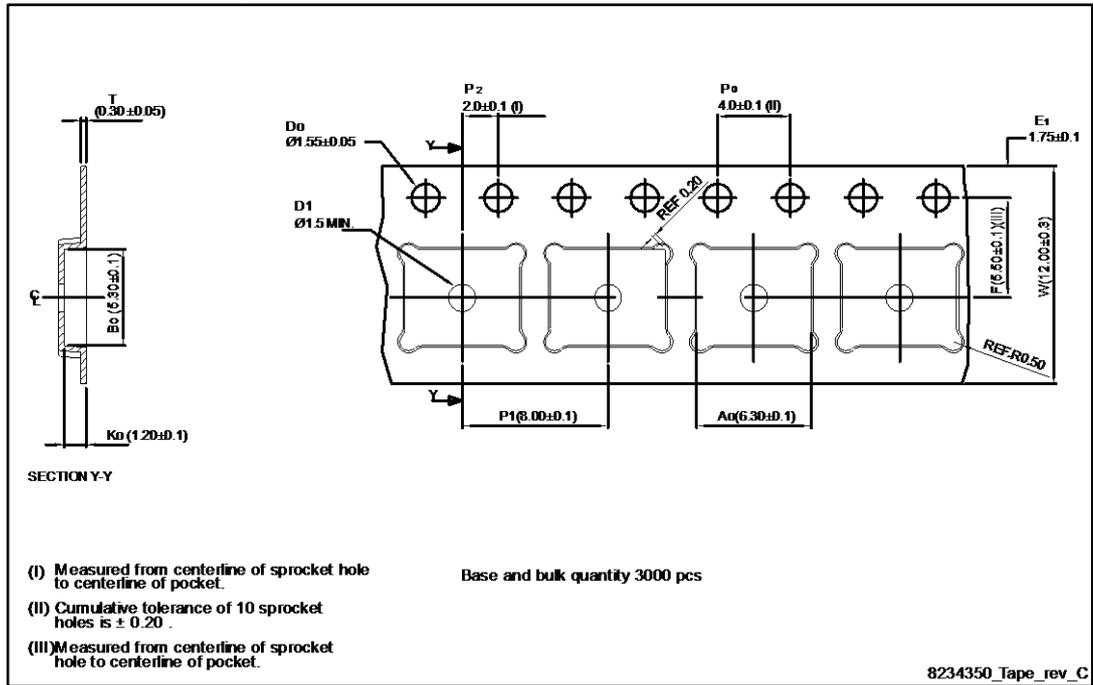


Figure 24: PowerFLAT™ 5x6 package orientation in carrier tape

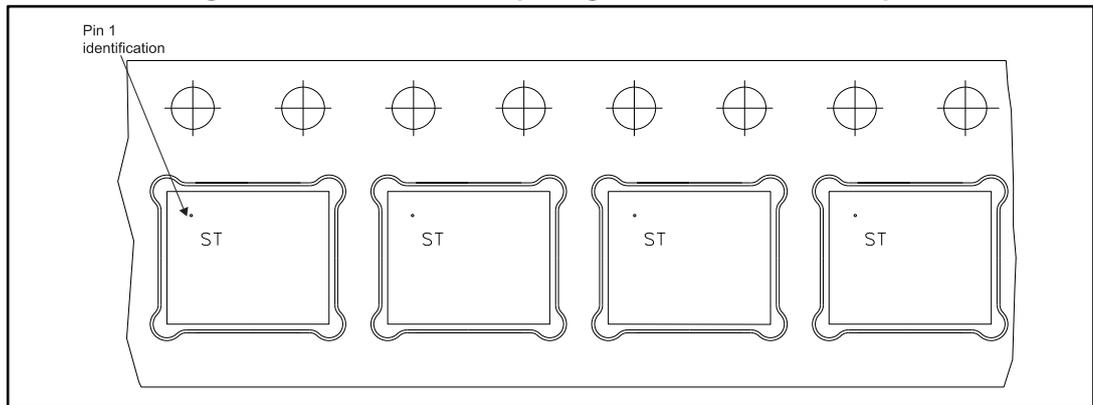
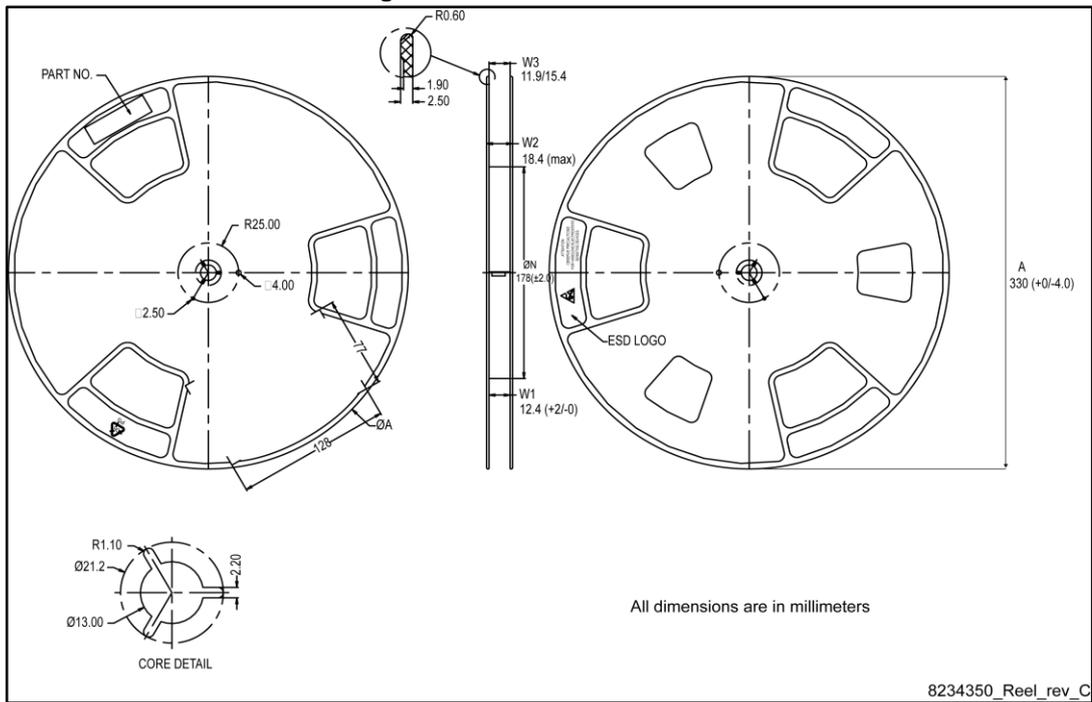


Figure 25: PowerFLAT™ 5x6 reel



5 Revision history

Table 11: Document revision history

Date	Revision	Changes
25-Sep-2015	1	First release.
09-Feb-2016	2	Modified: $R_{DS(on)}$ in cover page Modified: Table 2: "Absolute maximum ratings" , Table 3: "Thermal data" , Table 5: "On/off-state" , Table 6: "Dynamic" and Table 8: "Source-drain diode" Added: Section 3.1: "Electrical characteristics (curves)" Minor text changes

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